

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology
- ★ 100% EAS Guaranteed

Product Summary

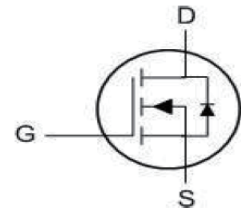
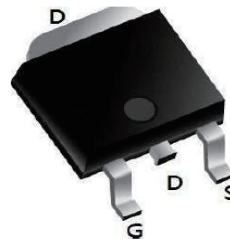
BVDSS	RDS(on)	ID
20V	3.7mΩ	80A

Description

The 80N02 is the high cell density trenched N-ch MOSFETs, which provide excellent RDS(on) and gate charge for most of the synchronous buck converter applications.

The 80N02 meet the RoHS and Green Product, requirement 100% EAS guaranteed with full function reliability approved.

TO252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	35	A
I_{DM}	Pulsed Drain Current ²	200	A
EAS	Single Pulse Avalanche Energy ³	58	mJ
I_{AS}	Avalanche Current	41	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	58	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	2.6	°C/W

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V,$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.4	0.7	1.1	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note ³	$V_{GS}=4.5V, I_D=30A$	-	3.7	5	m Ω
		$V_{GS}=2.5V, I_D=20A$	-	6.5	9	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V,$ $f = 1.0MHz$	-	2500	-	pF
C_{oss}	Output Capacitance		-	407	-	pF
C_{rss}	Reverse Transfer Capacitance		-	386	-	pF
Q_g	Total Gate Charge	$V_{DS}=10V, I_D=30A,$ $V_{GS}=4.5V$	-	32	-	nC
Q_{gs}	Gate-Source Charge		-	3	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	11	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=10V, I_D=30A,$ $R_{GEN}=3\Omega, V_{GS}=4.5V$	-	17	-	ns
t_r	Turn-on Rise Time		-	49	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	74	-	ns
t_f	Turn-off Fall Time		-	26	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	75	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	300	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_S=30A$	-	-	1.2	V

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: $T_J=25^\circ\text{C}, V_{DD}=10V, V_G=4.5V, L=0.5mH, R_G=25\Omega, I_{AS}=15A$
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Electrical and Thermal Characteristics (Curves)

Figure 1: Output Characteristics

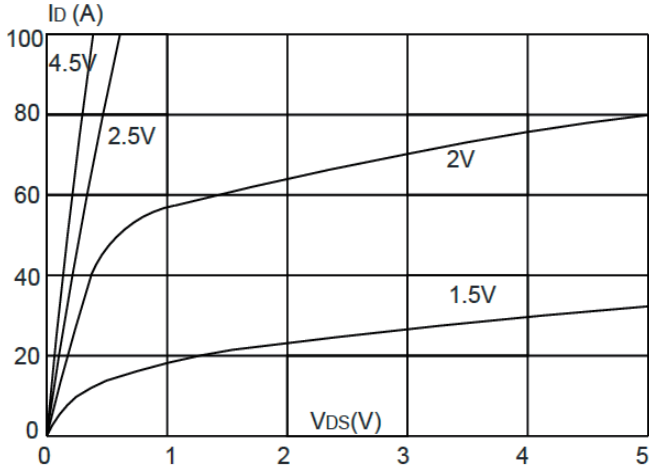


Figure 2: Typical Transfer Characteristics

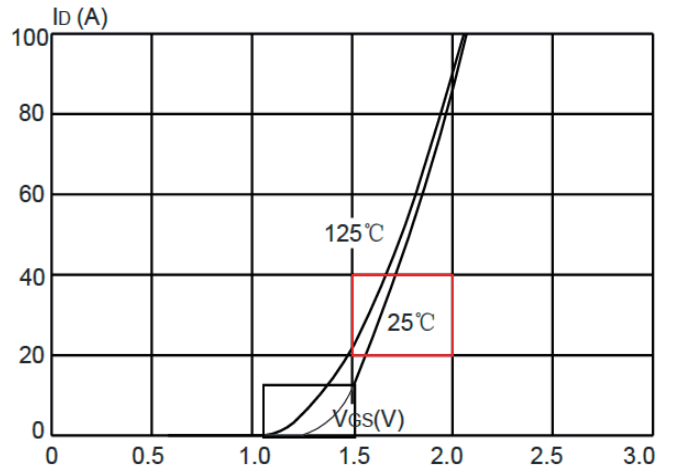


Figure 3: On-resistance vs. Drain Current

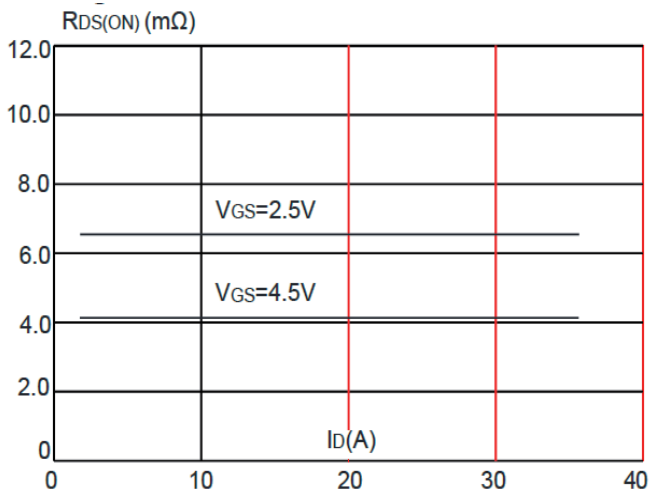


Figure 4: Body Diode Characteristics

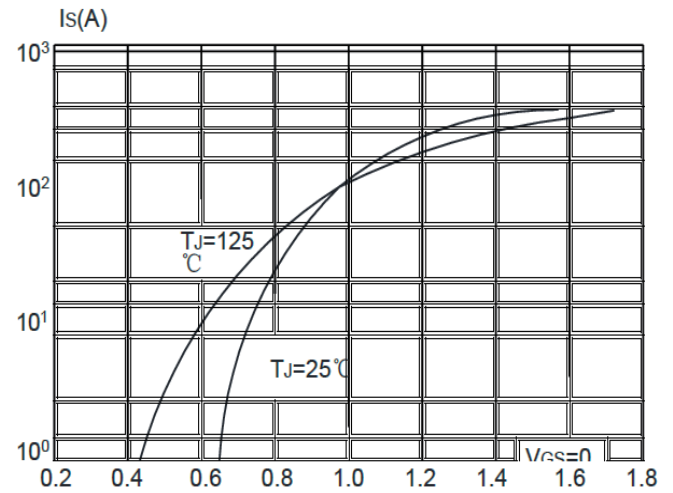


Figure 5: Gate Charge Characteristics

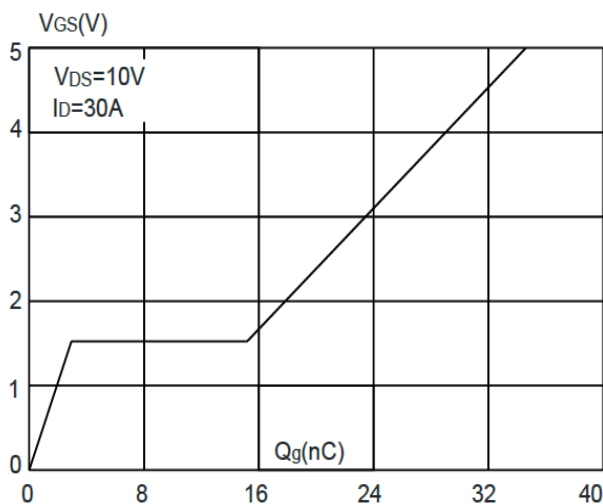
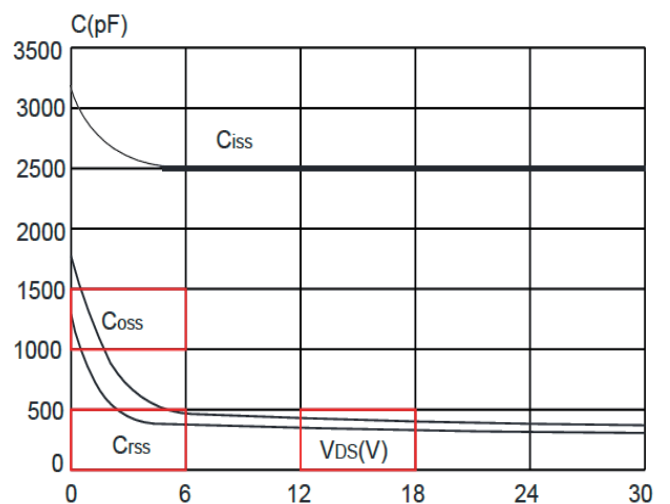


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

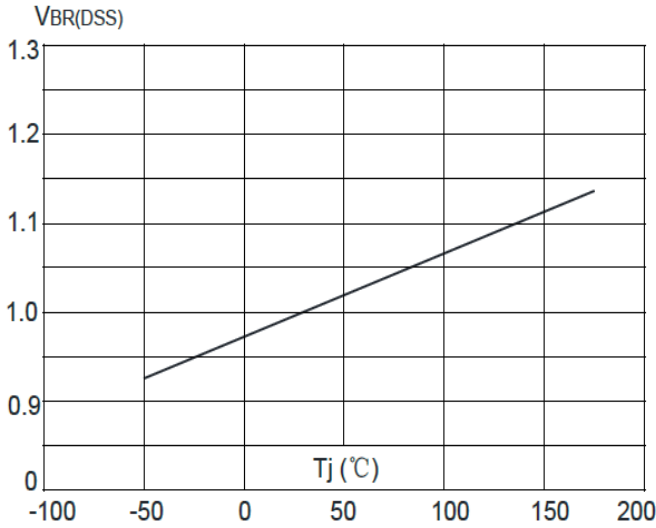


Figure 8: Normalized on Resistance vs. Junction Temperature

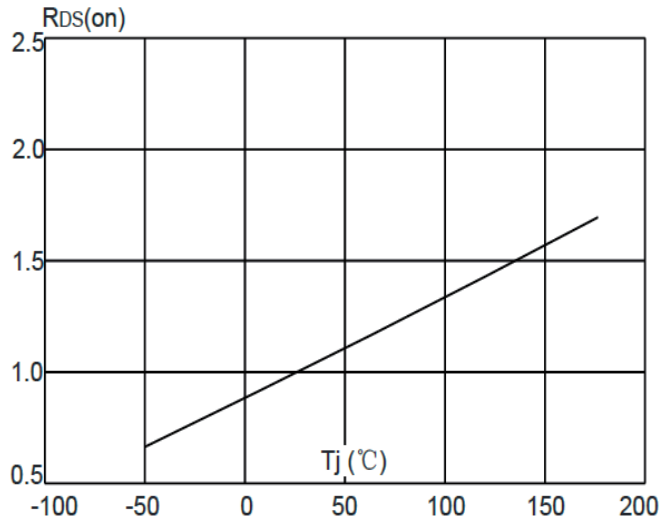


Figure 9: Maximum safe operating area

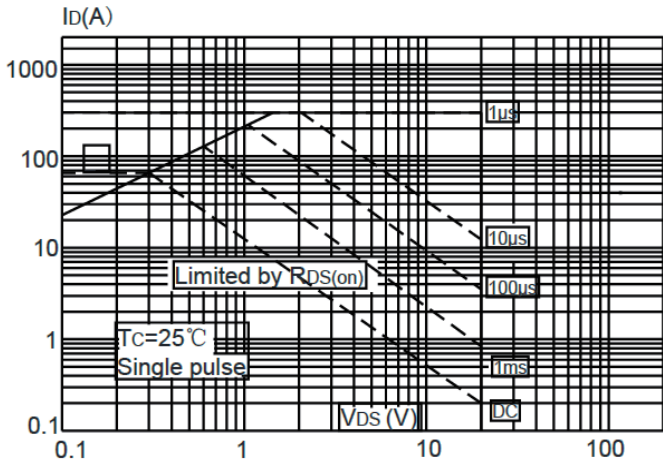


Figure 10: Maximum drain current vs. case temperature

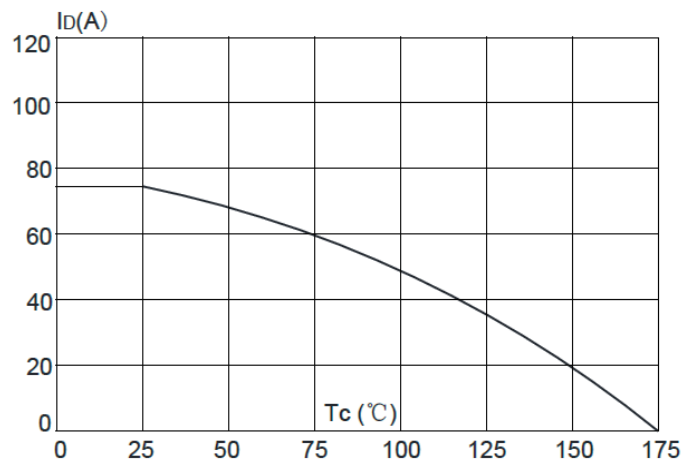
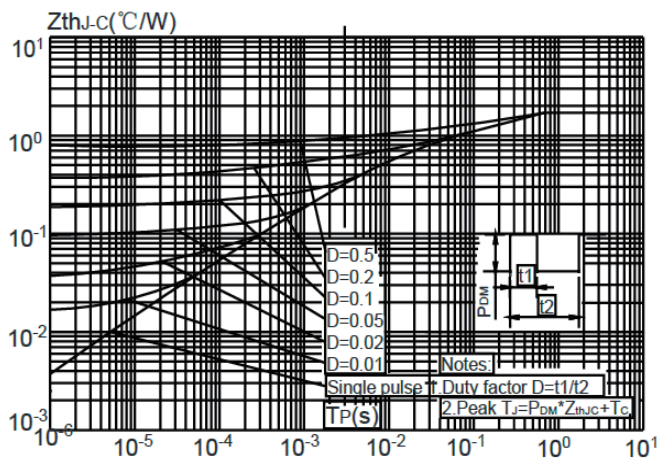
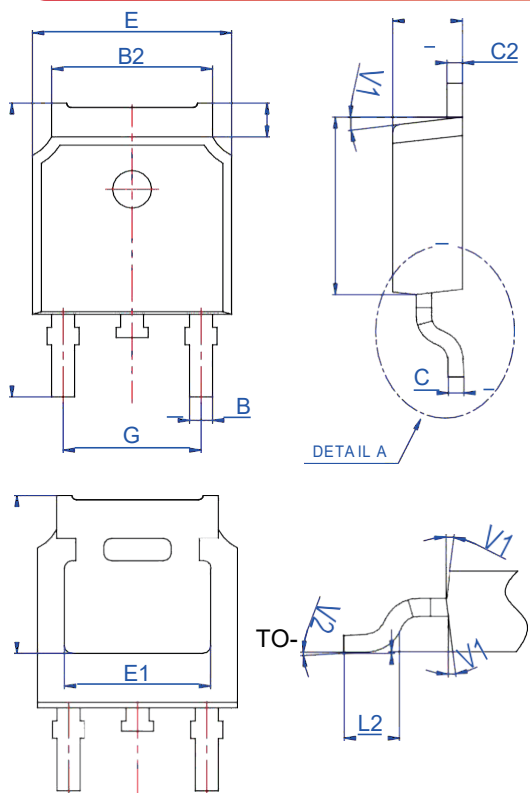


Figure 11: Maximum Effective Transient Thermal Impedance Junction to Case

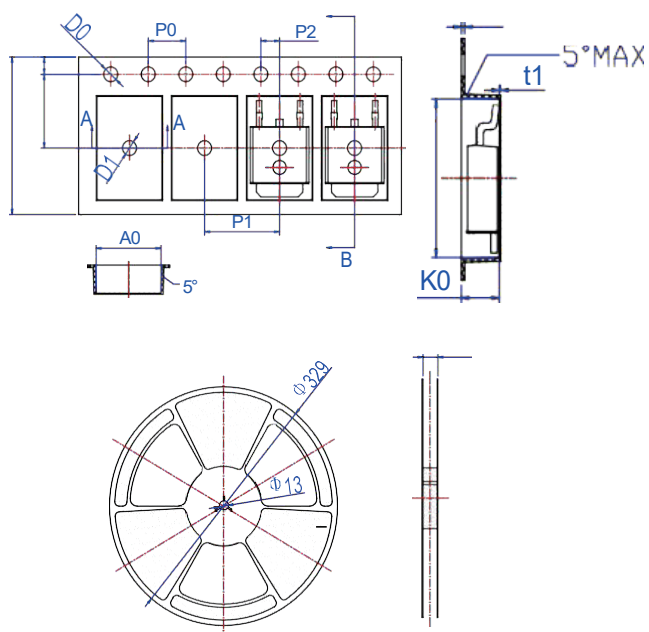


Package Mechanical Data-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.1		2.5	0.083		0.098
A2	0		0.1	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.4		0.6	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.9		6.3	0.232		0.248
D1	5.30REF			0.209REF		
E	6.4		6.8	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.5		10.7	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.9	16	16.1	0.626	0.63	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.4	7.5	7.6	0.291	0.295	0.299
D0	1.4	1.5	1.6	0.055	0.059	0.063
D1	1.4	1.5	1.6	0.055	0.059	0.063
P0	3.9	4	4.1	0.154	0.157	0.161
P1	7.9	8	8.1	0.311	0.315	0.319
P2	1.9	2	2.1	0.075	0.079	0.083
A0	6.85	6.9	7	0.27	0.271	0.276
B0	10.45	10.5	10.6	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.1			0.004		
10P0	39.8	40	40.2	1.567	1.575	1.583

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